# 24 and 40 Watt Peak Power Zener Transient Voltage Suppressors

# SOT-23 Dual Common Anode Zeners for ESD Protection

These dual monolithic silicon Zener diodes are designed for applications requiring transient overvoltage protection capability. They are intended for use in voltage and ESD sensitive equipment such as computers, printers, business machines, communication systems, medical equipment and other applications. Their dual junction common anode design protects two separate lines using only one package. These devices are ideal for situations where board space is at a premium.

#### **Features**

- SOT–23 Package Allows Either Two Separate Unidirectional Configurations or a Single Bidirectional Configuration
- Working Peak Reverse Voltage Range 3 V to 26 V
- Standard Zener Breakdown Voltage Range 5.6 V to 47 V
- Peak Power 24 or 40 W @ 1.0 ms (Unidirectional), per Figure 6 Waveform
- ESD Rating:
  - Class 3B (> 16 kV) per the Human Body Model
  - Class C (> 400 V) per the Machine Model
- ESD Rating of IEC61000-4-2 Level 4, ±30 kV Contact Discharge
- Maximum Clamping Voltage @ Peak Pulse Current
- Low Leakage < 5.0 μA
- Flammability Rating UL 94 V-0
- SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

#### **Mechanical Characteristics**

**CASE:** Void-free, transfer-molded, thermosetting plastic case

FINISH: Corrosion resistant finish, easily solderable

# **MAXIMUM CASE TEMPERATURE FOR SOLDERING PURPOSES:**

260°C for 10 Seconds

Package designed for optimal automated board assembly Small package size for high density applications Available in 8 mm Tape and Reel

Use the Device Number to order the 7 inch/3,000 unit reel. Replace the "T1" with "T3" in the Device Number to order the 13 inch/10,000 unit reel.

This document contains information on some products that are still under development. ON Semiconductor reserves the right to change or discontinue these products without notice.

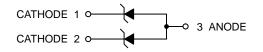


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SOT-23 CASE 318 STYLE 12



#### MARKING DIAGRAM



XXX = Specific Device Code

M = Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

#### **DEVICE MARKING INFORMATION**

See specific marking information in the device marking column of the table on page 3 of this data sheet.

#### **MAXIMUM RATINGS**

Rati	Symbol	Value	Unit	
Peak Power Dissipation @ 1.0 ms (Note 1) @ $T_L \le 25^{\circ}C$	MMBZ5V6ALT1G thru MMBZ9V1ALT1G MMBZ12VALT1G thru MMBZ47VALT1G	P <sub>pk</sub>	24 40	W
Total Power Dissipation on FR-5 Board (Note @ T <sub>A</sub> = 25°C Derate above 25°C	÷ 2)	P <sub>D</sub>	225 1.8	mW mW/°C
Thermal Resistance Junction-to-Ambient	$R_{ heta JA}$	556	°C/W	
Total Power Dissipation on Alumina Substrate  @ T <sub>A</sub> = 25°C Derate above 25°C	e (Note 3)	P <sub>D</sub>	300 2.4	mW mW/°C
Thermal Resistance Junction–to–Ambient		$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to +150	°C	
Lead Solder Temperature – Maximum (10 Se	cond Duration)	TL	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. Non-repetitive current pulse per Figure 6 and derate above  $T_A = 25$ °C per Figure 7.
- 2.  $FR-5 = 1.0 \times 0.75 \times 0.62$  in.
- 3. Alumina =  $0.4 \times 0.3 \times 0.024$  in, 99.5% alumina.

# **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MMBZ5V6ALT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
SZMMBZ5V6ALT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBZ5V6ALT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
MMBZ6VxALT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
SZMMBZ6VxALT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBZ6VxALT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
MMBZ9V1ALT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBZ9V1ALT13G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
MMBZxxVALT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
SZMMBZxxVALT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBZxxVALT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
SZMMBZxxVALT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
SZMMBZxxVTALT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

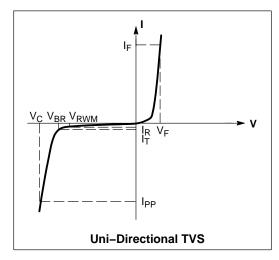
<sup>\*</sup>Other voltages may be available upon request.

#### **ELECTRICAL CHARACTERISTICS**

(T<sub>A</sub> = 25°C unless otherwise noted)

UNIDIRECTIONAL (Circuit tied to Pins 1 and 3 or 2 and 3)

Symbol	Parameter
I <sub>PP</sub>	Maximum Reverse Peak Pulse Current
V <sub>C</sub>	Clamping Voltage @ I <sub>PP</sub>
V <sub>RWM</sub>	Working Peak Reverse Voltage
I <sub>R</sub>	Maximum Reverse Leakage Current @ V <sub>RWM</sub>
V <sub>BR</sub>	Breakdown Voltage @ I <sub>T</sub>
Ι <sub>Τ</sub>	Test Current
ΘV <sub>BR</sub>	Maximum Temperature Coefficient of V <sub>BR</sub>
I <sub>F</sub>	Forward Current
V <sub>F</sub>	Forward Voltage @ I <sub>F</sub>
Z <sub>ZT</sub>	Maximum Zener Impedance @ I <sub>ZT</sub>
I <sub>ZK</sub>	Reverse Current
Z <sub>ZK</sub>	Maximum Zener Impedance @ I <sub>ZK</sub>



# **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

UNIDIRECTIONAL (Circuit tied to Pins 1 and 3 or Pins 2 and 3)

 $(V_F = 0.9 \text{ V Max } @ I_F = 10 \text{ mA}) (5\% \text{ Tolerance})$ 

**24 WATTS** 

				Breakdown Voltage				ax Zene ance (N		V <sub>C</sub> @			
	Device	V <sub>RWM</sub>	I <sub>R</sub> @ V <sub>RWM</sub>	V <sub>BF</sub>	(Note 4)	(V)	@ I <sub>T</sub>	Z <sub>ZT</sub> @ I <sub>ZT</sub>	Z <sub>ZK</sub> (	@ I <sub>ZK</sub>	v <sub>c</sub>	I <sub>PP</sub>	ΘV <sub>BR</sub>
Device*	Marking	Volts	μΑ	Min	Nom	Max	mA	Ω	Ω	mA	٧	Α	mV/°C
MMBZ5V6ALT1G/T3G	5A6	3.0	5.0	5.32	5.6	5.88	20	11	1600	0.25	8.0	3.0	1.26
MMBZ6V2ALT1G	6A2	3.0	0.5	5.89	6.2	6.51	1.0	-	-	-	8.7	2.76	2.80
MMBZ6V8ALT1G	6A8	4.5	0.5	6.46	6.8	7.14	1.0	-	_	_	9.6	2.5	3.4
MMBZ9V1ALT1G	9A1	6.0	0.3	8.65	9.1	9.56	1.0	_	-	-	14	1.7	7.5

 $(V_F = 0.9 \text{ V Max } @ I_F = 10 \text{ mA}) (5\% \text{ Tolerance})$ 

**40 WATTS** 

		l <sub>o</sub>		I <sub>R</sub> @ Breakdown Voltage			9	V <sub>C</sub> @ I <sub>PP</sub>		
	Device	V <sub>RWM</sub>	V <sub>RWM</sub>	V <sub>BF</sub>	(Note 4)	(V)	@ I <sub>T</sub>	V <sub>C</sub>	I <sub>PP</sub>	$\Theta V_{BR}$
Device*	Marking	Volts	nA	Min	Nom	Max	mA	V	Α	mV/°C
MMBZ12VALT1G	12A	8.5	200	11.40	12	12.60	1.0	17	2.35	7.5
MMBZ15VALT1G	15A	12	50	14.25	15	15.75	1.0	21	1.9	12.3
MMBZ16VALT1G	16A	13	50	15.20	16	16.80	1.0	23	1.7	13.8
MMBZ18VALT1G	18A	14.5	50	17.10	18	18.90	1.0	25	1.6	15.3
MMBZ20VALT1G	20A	17	50	19.00	20	21.00	1.0	28	1.4	17.2
MMBZ27VALT1G/T3G	27A	22	50	25.65	27	28.35	1.0	40	1.0	24.3
MMBZ33VALT1G	33A	26	50	31.35	33	34.65	1.0	46	0.87	30.4
MMBZ47VALT1G**	47A	38	50	44.65	47	49.35	1.0	50	0.74	42.3

 $(V_F = 0.9 \text{ V Max } @ I_F = 10 \text{ mA}) (2\% \text{ Tolerance})$ 

40 WATTS

			I <sub>R</sub> @	Breakdown Voltage			)	V <sub>C</sub> @ I <sub>PP</sub>	(Note 6)	
	Device	V <sub>RWM</sub>	V <sub>RWM</sub>	V <sub>BF</sub>	(Note 4)	(V)	@ I <sub>T</sub>	V <sub>C</sub>	I <sub>PP</sub>	$\Theta V_{BR}$
Device*	Marking	Volts	nA	Min	Nom	Max	mA	V	Α	mV/°C
MMBZ16VTALT1G	16T	13	50	15.68	16	16.32	1.0	23	1.7	13.8
MMBZ47VTALT1G**	47T	38	50	46.06	47	47.94	1.0	50	0.74	42.3

<sup>4.</sup> V<sub>BR</sub> measured at pulse test current I<sub>T</sub> at an ambient temperature of 25°C.
5. Z<sub>ZT</sub> and Z<sub>ZK</sub> are measured by dividing the AC voltage drop across the device by the AC current applied. The specified limits are for I<sub>Z(AC)</sub> = 0.1 I<sub>Z(DC)</sub>, with the AC frequency = 1.0 kHz.
6. Surge current waveform per Figure 6 and derate per Figure 7

<sup>\*</sup> Include SZ-prefix devices where applicable.

<sup>\*\*</sup>In development. Contact local sales rep for availability.

# **TYPICAL CHARACTERISTICS**

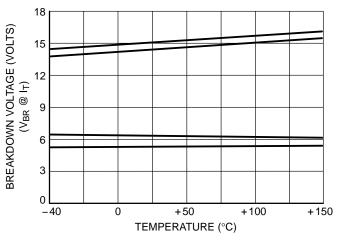


Figure 1. Typical Breakdown Voltage versus Temperature

(Upper curve for each voltage is bidirectional mode, lower curve is unidirectional mode)

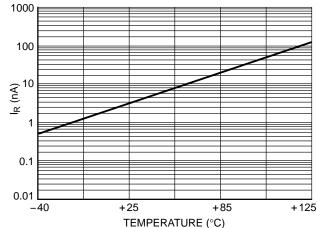


Figure 2. Typical Leakage Current versus Temperature

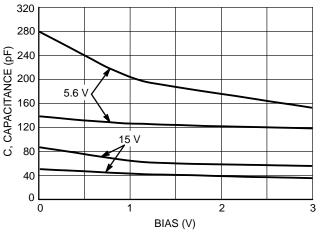


Figure 3. Typical Capacitance versus Bias Voltage
(Upper curve for each voltage is unidirectional mode,
lower curve is bidirectional mode)

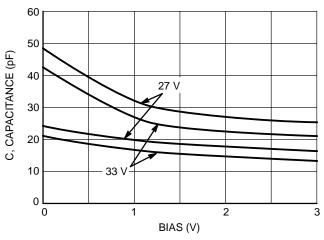


Figure 4. Typical Capacitance versus Bias Voltage (Upper curve for each voltage is unidirectional mode, lower curve is bidirectional mode)

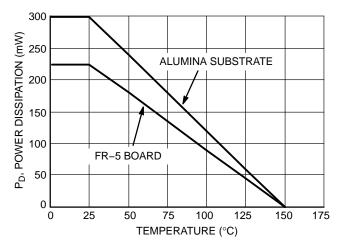


Figure 5. Steady State Power Derating Curve

# **TYPICAL CHARACTERISTICS**

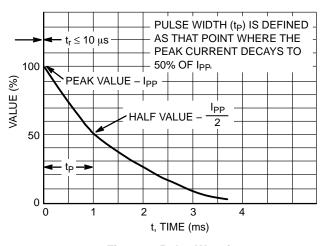


Figure 6. Pulse Waveform

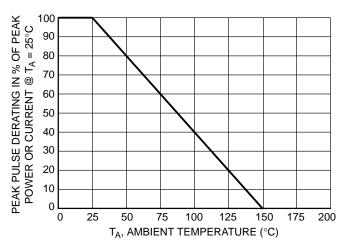


Figure 7. Pulse Derating Curve

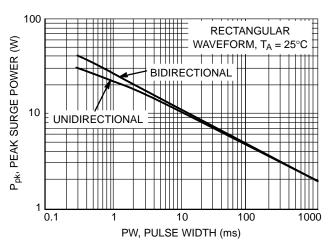


Figure 8. Maximum Non-repetitive Surge Power,  $P_{pk}$  versus PW

Power is defined as  $V_{RSM}\,x\,I_Z(pk)$  where  $V_{RSM}$  is the clamping voltage at  $I_Z(pk).$ 

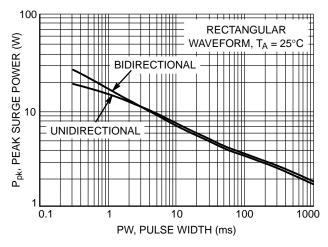


Figure 9. Maximum Non-repetitive Surge Power, Ppk(NOM) versus PW

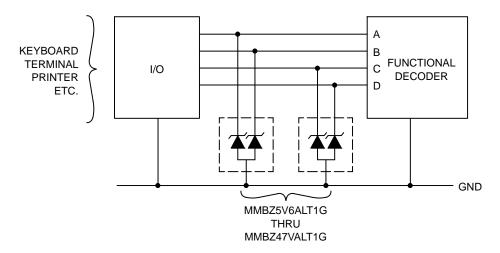
Power is defined as  $V_Z(NOM) \times I_Z(pk)$  where  $V_Z(NOM)$  is the nominal Zener voltage measured at the low test current used for voltage classification.

# **TYPICAL COMMON ANODE APPLICATIONS**

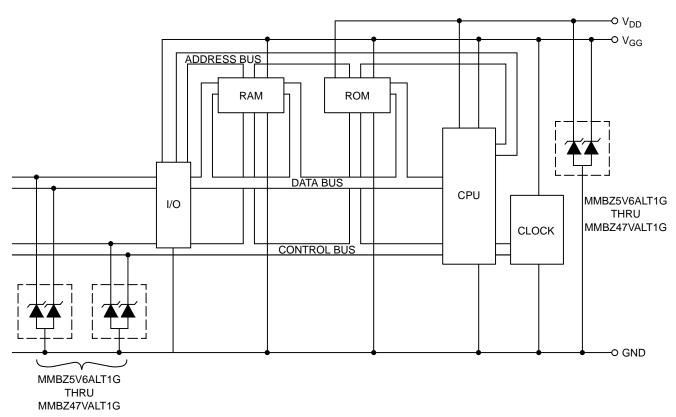
A dual junction common anode design in a SOT-23 package protects two separate lines using only one package. This adds flexibility and creativity to PCB design especially

when board space is at a premium. Two simplified examples of TVS applications are illustrated below.

# **Computer Interface Protection**

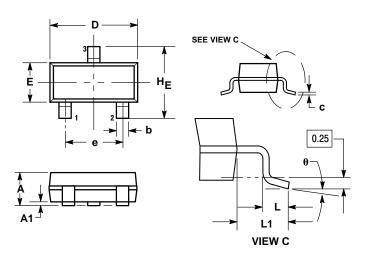


# **Microprocessor Protection**



#### PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 **ISSUE AP** 



#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
  MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS

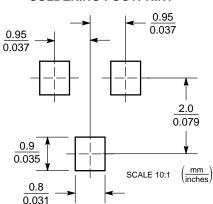
	М	ILLIMETE	RS	INCHES					
DIM	MIN	NOM	MAX	MIN	NOM	MAX			
Α	0.89	1.00	1.11	0.035	0.040	0.044			
A1	0.01	0.06	0.10	0.001	0.002	0.004			
b	0.37	0.44	0.50	0.015	0.018	0.020			
С	0.09	0.13	0.18	0.003	0.005	0.007			
D	2.80	2.90	3.04	0.110	0.114	0.120			
E	1.20	1.30	1.40	0.047	0.051	0.055			
е	1.78	1.90	2.04	0.070	0.075	0.081			
L	0.10	0.20	0.30	0.004	0.008	0.012			
L1	0.35	0.54	0.69	0.014	0.021	0.029			
HE	2.10	2.40	2.64	0.083	0.094	0.104			
θ	0°		10°	0°	-	10°			

STYLE 12:

PIN 1. CATHODE

- 2. CATHODE
- ANODE

#### **SOLDERING FOOTPRINT**



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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